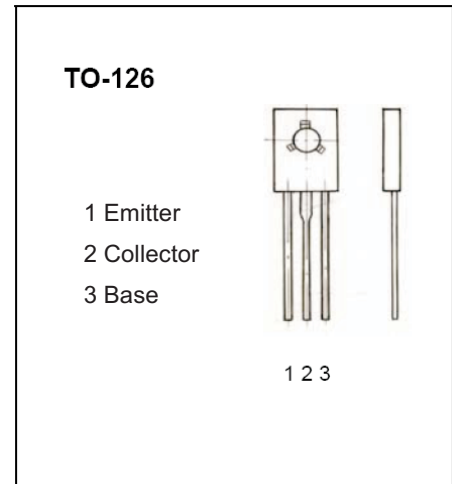


## PNP Silicon Transistor 2SB649A

### ■ Features

- Collector-Emitter Voltage :-160V
- Collector Current :-1.5A



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-180	V
Collector-emitter voltage	V <sub>CEO</sub>	-160	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-1.5	A
Collector power dissipation	P <sub>C</sub>	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55to +150	°C

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	V <sub>CB0</sub>	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-180			V
Collector-emitter voltage	V <sub>CEO</sub>	I <sub>C</sub> =-10mA, R <sub>BE</sub> =∞	-160			V
Emitter-base voltage	V <sub>EBO</sub>	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> =-160V, I <sub>E</sub> =0			-10	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-600mA, I <sub>B</sub> =-50mA			-1	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA			-1.5	V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-150mA	60		200	
		V <sub>CE</sub> =-5V, I <sub>C</sub> =-500mA	30			
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz		27		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-0.15A		140		MHz

### ■ hFE Classification

Rank	B	C
hFE	60 to 120	100 to 200